RENESAS HD74LVC2G53

2-channel Analog Multiplexer/Demultiplexer

REJ03D0156-0300 Rev.3.00 Jul.07.2005

Description

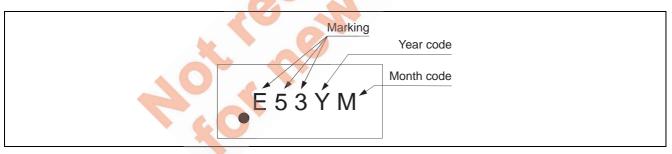
The HD74LVC2G53 has 2–channel analog multiplexer/demultiplexer in an 8 pin package. Applications include signal gating, chopping, modulation, or demodulation (modem), and signal multiplexing for analog to digital and digital to analog conversion systems. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as renesas uni logic series.
- Supply voltage range: 1.65 to 5.5 V
- Operating temperature range: -40 to $+85^{\circ}$ C
- Control inputs: VIH (Max.) = 5.5 V (@VCC = 0 V to 5.5 V)
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LVC2G53CPE	WCSP-8 pin	SXBG0008KA-A (TBS-8V)	СР	E (3,000 pcs/reel)
HD74LVC2G53CLE		SXBG0008KB-A (TBS-8AV)	CL	

Article Indication



Function Table

Contro	Control inputs					
INH	А	On channel				
Н	X	None				
L	Н	Y ₁				
L	L	Y ₀				

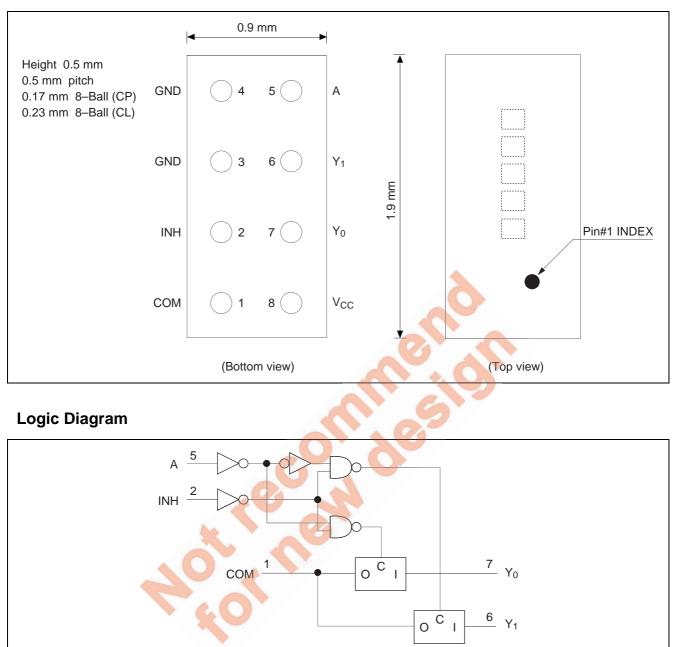
H : High level

L : Low level

X : Immaterial



Pin Arrangement





Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{cc}	-0.5 to 6.5	V	
Input voltage range *1	VI	-0.5 to 6.5	V	
Output voltage range *1, 2	Vo	–0.5 to V _{CC} +0.5	V	Output : H or L
Input clamp current	I _{IK}	-50	mA	V ₁ < 0
Output clamp current	Ι _{ΟΚ}	-50	mA	V ₀ < 0
Continuous output current	Ι _Ο	±50	mA	$V_{O} = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±100	mA	
Package Thermal impedance	θ _{ja}	140	°C/W	СР
	-	102		CL
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This value is limited to 5.5 V maximum.

Recommended Operating Conditions

ltem	Symbol	Min	Max	Unit	Conditions
Supply voltage range	Vcc	1.65	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	Vo	0	V _{cc}	V	
Input transition rise or fall rate	Δt / Δv	0	20 10 10	ns / V	$V_{CC} = 1.65 \text{ to } 1.95 \text{ V},$ 2.3 to 2.7 V $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$
Operating free-air temperature	Ta	-40	85	°C	VCC = 4.5 10 5.5 V

Note: Unused or floating inputs must be held high or low.

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Electrical Characteristics

• Ta = -40 to $85^{\circ}C$

ltem	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test condition
Input voltage	VIH	1.65 to 1.95	V _{CC} ×0.65		_	V	Control input only.
		2.3 to 2.7	V _{CC} ×0.7				
		3.0 to 3.6	V _{CC} ×0.7				
		4.5 to 5.5	V _{CC} ×0.7				
	VIL	1.65 to 1.95			V _{CC} ×0.35		
		2.3 to 2.7			V _{CC} ×0.3		
		3.0 to 3.6			V _{CC} ×0.3		
		4.5 to 5.5			V _{CC} ×0.3		
On-state switch	R _{ON}	1.65	_	13	30	Ω	$I_{S} = 4 \text{ mA}$
resistance		2.3	_	10	20		$I_{\rm S} = 8 \mathrm{mA}$
		3.0	_	8.5	17		$I_{\rm S} = 24 \text{ mA}$ $V_{\rm I} = V_{\rm CC} \text{ or GND}$
		4.5	_	6.5	13		I _S = 32 mA
Peak on resistance	R _{ON} (P)	1.65	_	86.5	120		$I_{S} = 4 \text{ mA}$
		2.3	_	23	30		$I_{\rm S} = 8 \mathrm{mA}$
		3.0	_	13	20		$I_{\rm S} = 24 \text{ mA}$ $V_{\rm I} = V_{\rm CC} \text{ to GND}$
		4.5	_	8	15		I _S = 32 mA
Difference of	ΔR_{ON}	1.65	_	_	7		$I_{S} = 4 \text{ mA}$
on-state resistance		2.3	_	_ //	5		$I_{\rm S} = 8 \mathrm{mA}$
between switches		3.0	_		3		$I_{\rm S} = 24 \text{ mA}$ $V_{\rm I} = V_{\rm CC} \text{ to GND}$
		4.5	_		2		I _S = 32 mA
Off-state switch	I _{S (OFF)}	5.5	—	A	±1.0	μA	$V_{I} = V_{CC}$ and $V_{O} = GND$ or
leakage current	. ,		_		±0.1*1		$V_1 = GND$ and $V_0 = V_{CC}$,
							$V_{\rm INH} = V_{\rm IH}$
On-state switch	I _{S (ON)}	5.5	E	-	±1.0	μΑ	$V_I = V_{CC}$ or GND,
leakage current				-	±0.1* ¹		$V_{\rm INH} = V_{\rm IL}$
A			5				V _o = Open
Control input	I _{IN}	5.5			±1.0	μA	$V_{IN} = V_{CC}$ or GND
current					±0.1* ¹		
Quiescent	Icc	5.5		—	10	μA	$V_{IN} = V_{CC}$ or GND
supply current					1.0* ¹		
	Δlcc	5.5	_		500	μA	$V_{\rm C} = V_{\rm CC} - 0.6 \text{ V}$
Control input capacitance	CIC	5.0	_	3.5	—	pF	
Switch terminal	CI/O(OFF)	5.0	_	6.5		pF	Y
capacitance				10	_]	СОМ
	CI/O(ON)	5.0	_	14.0	_		

Note: 1. Ta = 25°C



Switching Characteristics

• $V_{CC} = 1.8 \pm 0.15 V$

		Ta = -40 to 85°C			Test	FROM	то
Item	Symbol	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation delay time*1	t _{PLH} , t _{PHL}		2.0	ns	C_L = 30 pF, R_L = 1.0 k Ω	COM or Yn	Yn or COM
Enable time	t _{ZH} , t _{ZL}	3.3	9.0		$C_L = 30 \text{ pF}, \text{ R}_L = 1.0 \text{ k}\Omega$	INH	COM or Yn
Disable time	t_{HZ},t_{LZ}	3.2	10.9		$C_L = 30 \text{ pF}, R_L = 1.0 \text{ k}\Omega$	INH	COM or Yn
Enable time	t_{ZH}, t_{ZL}	2.9	10.3		$C_L = 30 \text{ pF}, R_L = 1.0 \text{ k}\Omega$	A	Yn
Disable time	t _{HZ} , t _{LZ}	2.1	9.4		$C_L = 30 \text{ pF}, \text{ R}_L = 1.0 \text{ k}\Omega$	A	Yn

• $V_{CC} = 2.5 \pm 0.2 V$

		Ta = -40 to 85°C			Test	FROM	ТО
ltem	Symbol	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation delay time*1	t _{PLH} , t _{PHL}		1.2	ns	$C_L = 30 \text{ pF}, \text{ R}_L = 500 \Omega$	COM or Yn	Yn or COM
Enable time	t_{ZH}, t_{ZL}	2.5	6.1		$C_{L} = 30 \text{ pF}, R_{L} = 500 \Omega$	INH	COM or Yn
Disable time	t_{HZ},t_{LZ}	2.3	9.3		$C_{L} = 30 \text{ pF}, R_{L} = 500 \Omega$	INH	COM or Yn
Enable time	t_{ZH}, t_{ZL}	2.1	7.2		$C_{L} = 30 \text{ pF}, R_{L} = 500 \Omega$	A	Yn
Disable time	t_{HZ}, t_{LZ}	1.4	7.9		$C_{L} = 30 \text{ pF}, R_{L} = 500 \Omega$	A	Yn

• $V_{CC} = 3.3 \pm 0.3 V$

		Ta = -40	Ta = -40 to 85°C		Test	FROM	то
Item	Symbol	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation delay time*1	t _{PLH} , t _{PHL}	_	0.8	ns	$C_L = 50 \text{ pF}, R_L = 500 \Omega$	COM or Yn	Yn or COM
Enable time	t _{ZH} , t _{ZL}	2.2	5.4		$C_{L} = 50 \text{ pF}, R_{L} = 500 \Omega$	INH	COM or Yn
Disable time	t _{HZ} , t _{LZ}	2.3	8.1		$C_{L} = 50 \text{ pF}, R_{L} = 500 \Omega$	INH	COM or Yn
Enable time	t _{ZH} , t _{ZL}	1.9	5.8		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	A	Yn
Disable time	t _{HZ} , t _{LZ}	1.1	7.2		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	A	Yn
• $V_{CC} = 5.0 \pm 0.5 \text{ V}$			~0				

(3)

• $V_{CC} = 5.0 \pm 0.5 \text{ V}$

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	Ta = -40	Ta = -40 to 85°C		Test	FROM	то
Symbol	Min	Max	Unit	Conditions	(Input)	(Output)
t _{PLH} , t _{PHL}		0.6	ns	$C_L = 50 \text{ pF}, \text{ R}_L = 500 \Omega$	COM or Yn	Yn or COM
t _{ZH} , t _{ZL}	1.8	4.5		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	INH	COM or Yn
t _{HZ} , t _{LZ}	1.6	8.0		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	INH	COM or Yn
t _{ZH} , t _{ZL}	1.3	5.4		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	A	Yn
t _{HZ} , t _{LZ} *	1.0	5.0		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	A	Yn
	tplh, tphl tzh, tzl thz, tlz tzh, tzl	Symbol Min t _{PLH} , t _{PHL} - t _{ZH} , t _{ZL} 1.8 t _{HZ} , t _{LZ} 1.6 t _{ZH} , t _{ZL} 1.3	Symbol Min Max t _{PLH} , t _{PHL} 0.6 t _{ZH} , t _{ZL} 1.8 4.5 t _{HZ} , t _{ZL} 1.6 8.0 t _{ZH} , t _{ZL} 1.3 5.4	Symbol Min Max Unit tPLH, tPHL - 0.6 ns tZH, tZL 1.8 4.5 1.4 tHZ, tLZ 1.6 8.0 1.3 tZH, tZL 1.3 5.4 1.3	$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	Symbol Min Max Unit Conditions (Input) t_{PLH}, t_{PHL} - 0.6 ns $C_L = 50 \text{ pF}, R_L = 500 \Omega$ COM or Yn t_{ZH}, t_{ZL} 1.8 4.5 $C_L = 50 \text{ pF}, R_L = 500 \Omega$ INH t_{HZ}, t_{LZ} 1.6 8.0 $C_L = 50 \text{ pF}, R_L = 500 \Omega$ INH t_{ZH}, t_{ZL} 1.3 5.4 $C_L = 50 \text{ pF}, R_L = 500 \Omega$ A

Notes: 1. The propagation delay is calculated RC time constant of typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

Analog Switch Characteristics

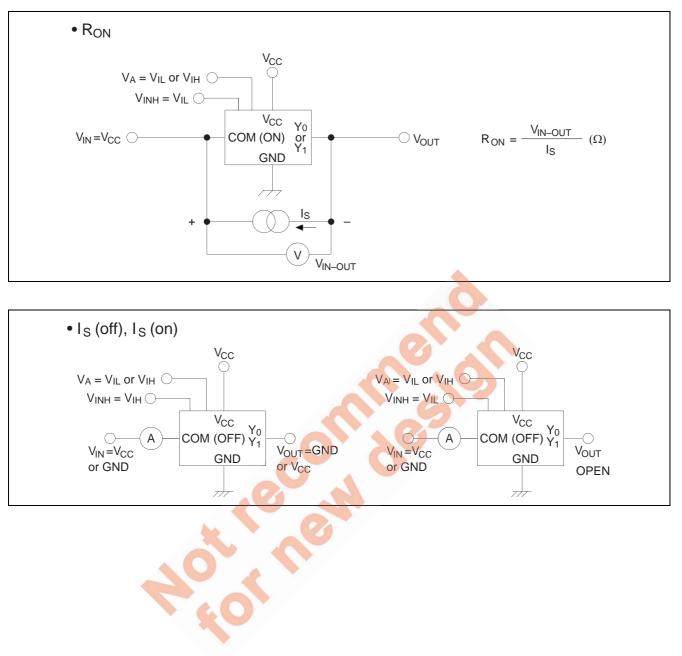
		Т	a = 25°	С				FROM	то
ltem	V _{cc} (V)	Min	Тур	Max	Unit	Te	est conditions	(Input)	(Output)
Frequency response	1.65	_	35	_	MHz	$C_{L} = 50 \text{ pF},$	Adjust fin voltage to	COM or Y	Y or COM
(Switch ON)	2.3	_	120	_		$R_L = 600 \ \Omega$	obtain 0dBm at output		
	3.0	_	190	_			when fin is 1MHz (sine		
	4.5	_	215	_			wave).		
	1.65	_	>300	_		$C_L = 5 \text{ pF},$	Increase fin frequency		
	2.3	_	>300	_		$R_L = 50 \ \Omega$	until the dB-meter		
	3.0		>300				reads –3 dBm.		
	4.5		>300				$20 \log(V_0/V_1) = -3 \text{ dBm}$		
Crosstalk	1.65	_	-58	_	dB	C∟ = 50 pF,	Adjust fin voltage to	COM	Y
(between switches)	2.3	_	-58	_		$R_L = 600 \ \Omega$	obtain 0dBm at input		
	3.0	_	-58	_			when fin is 1MHz (sine		
	4.5	_	-58	_			wave).		
	1.65	_	-42	_		$C_L = 5 \text{ pF},$			
	2.3	_	-42	_		$R_L = 50 \Omega$			
	3.0	_	-42	_					
	4.5	_	-42	_					
Crosstalk	1.65	_	35	_	mV	$C_{L} = 50 \text{ pF},$	Adjust RL value to	INH	COM or Y
(Control input to signal	2.3	_	50	_		$R_L = 600 \Omega$	obtain 0A at I _{IN/OUT}		
output)	3.0	_	70	_			when fin is 1MHz		
	4.5	_	100	_			(square wave)	Ĩ	
Feed through	1.65		-60		dB	$C_{L} = 50 pF$,	Adjust fin voltage to	COM or Y	Y or COM
attenuation	2.3	_	-60	_		$R_L = 600 \Omega$	obtain 0dBm at input		
(Switch OFF)	3.0		-60				wh <mark>en fin</mark> is 1MHz		
	4.5	_	-60	—			(sine-wave)		
	1.65	_	-50	_	\square	$C_L = 5 pF$,			
	2.3	_	-50			$R_L = 50 \Omega$			
	3.0	_	-50	T					
	4.5	_	-50	24					
Sine-wave distortion	1.65	—	0.1		%	$C_L = 50 \text{ pF},$	V _I =1.4V _{P-P} , V _{CC} =1.65V	COM or Y	Y or COM
	2.3		0.025	/		$R_L = 10 \ k\Omega$	V _I =2.0V _{P-P} , V _{CC} =2.3V		
	3.0		0.015	-		fin = 1kHz	V _I =2.5V _{P-P} , V _{CC} =3.0V		
	4.5	0	0.01	T		(sine-wave)	V _I =4.0V _{P-P} , V _{CC} =4.5V		
	1.65	-	0.15	_		C _L = 50 pF,	1		
	2.3		0.025	-		$R_L = 10 \text{ k}\Omega$			
	3.0	-4	0.015	-	1	fin = 10kHz			
	4.5		0.01	_	1	(sine-wave)			

Operating Characteristics

				Ta = 25°C			
ltem	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test Conditions
Power dissipation	C _{PD}	1.8	_	9	_	pF	f = 10 MHz
capacitance		2.5		10			
		3.3		10			
		5.0	_	12	_		

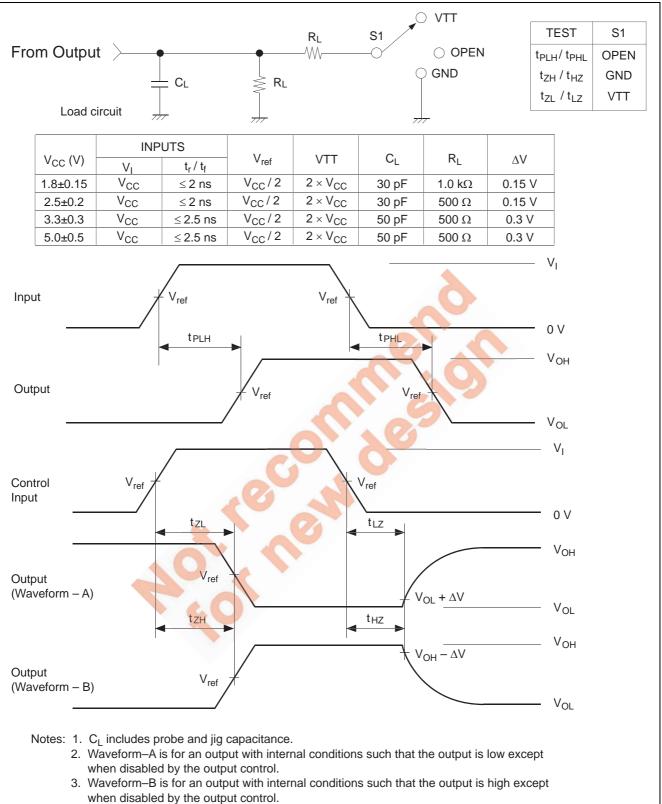


Test Circuit



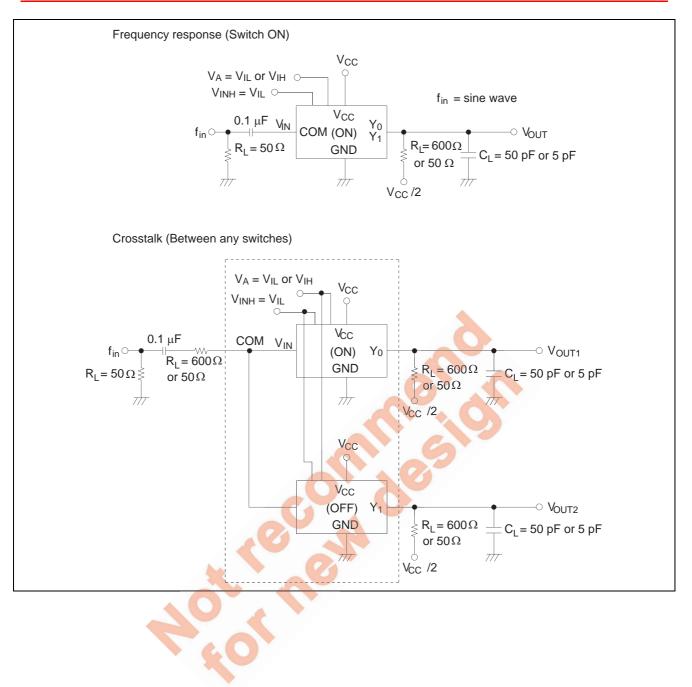


Test Circuit (cont.)

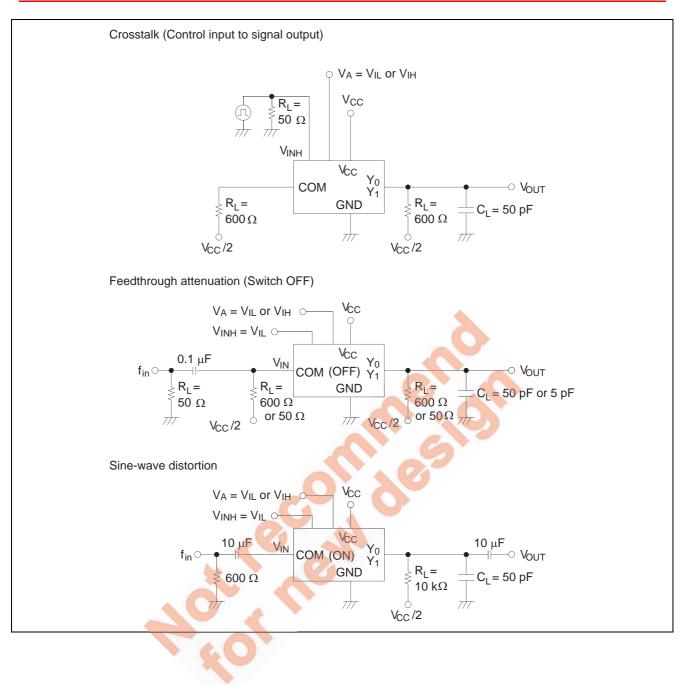


- 4. All input pulses are supplied by generators having the following characteristics: PRR \leq 10MHz, Zo = 50 $\Omega.$
- 5. The output are measured one at a time with one transition per measurement.

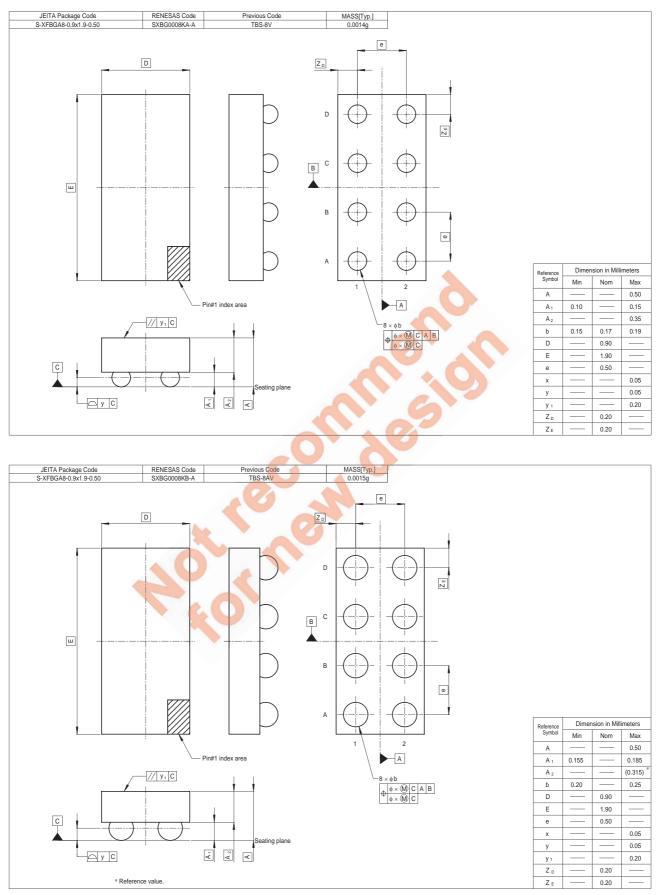








Package Dimensions





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